

ESA-QCA0068T-C



**TOTAL DOSE RADIATION
TEST REPORT
No. HUY-RR-TL-038**

Issue: 1 Rev.:
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SCC Component No.: HUYTL05503B		Component Designation: OP400 AY	Irradiation Spec. No.: ESA/SCC 22900 Iss. 3
Gen. Spec.: SCC 9000 8 Det. Spec.: HUY-SP-TL-055 1 Amend.:		Evaluation: - Acceptance Diffusion: - Acceptance Lot: X	Project/Programme: HUYGENS
Family: 08	Group: 09	Functional Assignment: QUAD OPERATIONAL AMPLIFIER	Package: DIL 14
Manuf. Name: Analog Devices Address: SANTA CLARA (USA)		Irradiation Facility: CIEMAT Address: MADRID (SPAIN)	Test House: TECNOLOGICA Address: MADRID (SPAIN)
Radiation Test Plan No.: HUY-IP-TL-038		Sample Size: 5 Irradiation Devices: 4 Control Devices: 1	Date Code: 9342 Diffusion LOT: 2F12250.1 Wafer N°: 9, 22
Radiation Source: Cobalt-60		Energy: 1,33/1,17 MeV Average Dose Rate: 10,263 Krad/h	Date of Test: 11/94

Electrical Measurements. Parameters Tested:

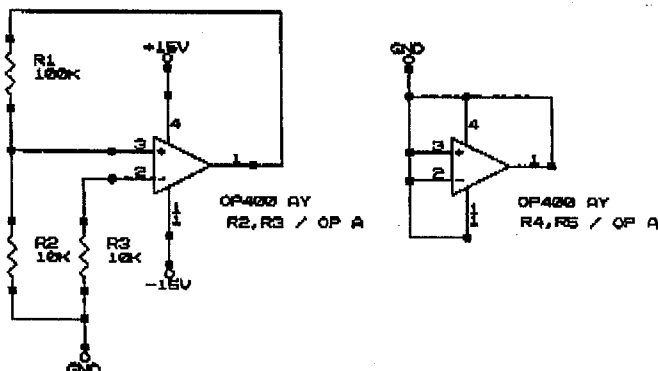
Input Offset Voltage (V_{OS}), Input Offset Current (I_{OS}), Input Bias Current (I_B), Power Supply Rejection Ratio (PSRR), Large Signal Voltage Gain 1 (A_{V01}), Large Signal Voltage Gain 2 (A_{V02}), Supply Current (I_S) and Slew Rate (SR+ & SR-).

Irradiation Conditions:
Biased: Y
Test Circuit: Figure 1

Irradiation Measurements Interval:
Biased: N
Test Circuit: N/A

Annealing Tests: YES
Biased: Y
Time: 90h / 96h
Temp.: 25°C / 25°C
Test Circuit: Figure 1

Figure 1:



Irradiat. Respons.: J. VAQUERO
Date: 28/11/94
Signature: _____

Electr. Test Resp.: J. M. VALERDE
Date: 29/11/94
Signature: _____

Approved by QA: J. ALARCO
Date: 29/11/94
Signature: _____



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CONCLUSION

The results indicates that:

- Input offset current measurements pass during all irradiation steps but fail during annealing in one device (RS) biased with second bias circuit.
- Input bias current measurements fail at 10 Krads on all op amp and recover slightly during annealing. Operational biased with second circuit are more affected during the test.
- PSRR measurements fail at 10 Krads on all op amp and recover during annealing. Operational biased with second circuit are more affected during the test and have worse recover during annealing.
- Open loop gain measurements have low dependence with biasing circuit:
AVO1 fails at 10 Krads in all op amp and recover during annealing in first bias circuit.
AVO2 fails between 20 and 30 Krads and recover under spec during annealing in first bias circuit.
- Slew rate measurements fail between 5 and 10 Krads and don't recover during annealing in both bias circuits.
- All other measurements remains under spec during all the irradiation test.




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SCHEDULE

Test Step	Description	Result or Actual Test Condition	Time in	Time Out	Exposure
1	Sample serialization	CONTROL R1. IRR. DEVICES R2,R3,R4,R5.			
2	Initial Electrical Measurements	See 0 krad(Si) values in respective Parameter Data Tables Temperature: 20,1°C Humidity: 40,2%	08:45 17/11	09:20 17/11	35 min.
3	Set-up of Test	Bias circuit verified according to Fig. 1			
4	Irradiation Exposure	Dose: 5,145 Krad(Si) Cumulative Dose: 5,145 Krad(Si) Dose Rate: 10,29 Krad(Si)/h Temperature: 23,7 °C	09:35	10:05	30 min.
5	Intermediate Electrical Measurements	See 5 Krad(Si) values in respective Parameter Data Tables Temperature: 21,7°C Humidity: 36,8%	10:10	10:31	21 min.
6	Set-up of Test	Bias circuit verified according to Fig. 1			
7	Irradiation Exposure	Dose: 5,14 Krad(Si) Cumulative Dose: 10,285 Krad(Si) Dose Rate: 10,28 Krad(Si)/h Temperature: 23,5°C	10:40	11:10	30 min.
8	Intermediate Electrical Measurements	See 10 krad(Si) values in respective Parameter Data Tables Temperature: 21,9°C Humidity: 37,5%	11:15	11:40	25 min.
9	Set-up of Test	Bias circuit verified according to Fig. 1			
10	Irradiation Exposure	Dose: 5,105 Krad(Si) Cumulative Dose: 15,39 krad(Si) Dose Rate: 10,21 Rad(Si)/h Temperature: 23,6°C	11:45	12:15	30 min.

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Test Step	Description	Result or Actual Test Condition	Time in	Time Out	Exposure
11	Intermediate Electrical Measurements	See 15 Krad(Si) values in respective Parameter Data Tables Temperature: 22,5°C Humidity: 35,5%	12:20	12:35	15 min.
12	Set-up of Test	Bias circuit verified according to Fig. 1			
13	Irradiation Exposure	Dose: 5,105 Krad(Si) Cumulative Dose: 20,495 Krad(Si) Dose Rate: 10,21 Rad(Si)/h Temperature: 23,7°C	12:45	13:15	30 min.
14	Intermediate Electrical Measurements	See 20 Krad(Si) values in respective Parameter Data Tables Temperature: 22,5°C Humidity: 35,8%	13:20	13:40	20 min.
15	Set-up of Test	Bias circuit verified according to Fig. 1			
16	Irradiation Exposure	Dose: 10,24 Krad(Si) Cumulative Dose: 30,735 Krad(Si) Dose Rate: 10,24 Rad(Si)/h Temperature: 23,7°C	13:46	14:46	60 min.
17	Intermediate Electrical Measurements	See 30 Krad(Si) values in respective Parameter Data Tables Temperature: 22,1°C Humidity: 40.6%	14:55	15:50	55 min.
18	Annealing	Bias circuit verified according to Fig. 1. Temperature: 19,5°C (average)	16:00 17/11	08:30 21/11	89:30 h.
19	Electrical Measurements	See Ann1 values in respective Parameter Data Tables Temperature: 16,6 °C Humidity: 43.1%	08:30	09:20	50 min.
20	Annealing	Bias circuit verified according to Fig. 1. Temperature: 18°C (average)	09:20 21/11	09:20 25/11	96 h.



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Test Step	Description	Result or Actual Test Condition	Time in	Time Out	Exposure
21	Electrical Measurements	See Ann2 values in respective Parameter Data Tables Temperature: 20°C Humidity: 40,6%	09:30	10:30	60 min.

